### 503158399 01/30/2015

## PATENT ASSIGNMENT COVER SHEET

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SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

#### **CONVEYING PARTY DATA**

Name	Execution Date
Shao-Wei Wang	01/27/2015
Shu-Ming Yeh	01/27/2015
Yu-Tung Hsiao	01/27/2015

#### **RECEIVING PARTY DATA**

Name:	UNITED MICROELECTRONICS CORP.
Street Address:	No.3, Li-Hsin Road 2, Science-Based Industrial Park
City:	Hsin-Chu City
State/Country:	TAIWAN

### **PROPERTY NUMBERS Total: 1**

Property Type	Number
Application Number:	14609446

#### **CORRESPONDENCE DATA**

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using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

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**Correspondent Name:** WINSTON HSU **Address Line 1:** P.O.BOX 506

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ATTORNEY DOCKET NUMBER:	NAUP2405USA
NAME OF SUBMITTER:	KATE YEH
SIGNATURE:	/KATE YEH/
DATE SIGNED:	01/30/2015

#### **Total Attachments: 6**

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PATENT 503158399 REEL: 034849 FRAME: 0423

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PATENT REEL: 034849 FRAME: 0424

# COMBINE DECLARATION (37 CFR 1.63) FOR UTILITY OR DESIGN APPLICATION USING AN APPLICATION DATA SHEET (37 CFR 1.76) AND ASSIGNMENT

#### Title of Invention:

## SEMICONDUCTOR STRUCTURE WITH A MULTILAYER GATE OXIDE AND METHOD OF FABRICATING THE SAME

As the below named inventor, I here This declaration is directed to:	by declare that:			
☑ The attached application, or				
☐ United States application number		_filed on,	or	
☐ PCT international application	number	filed on		
The above-identified application was	s made or authorized to be made	by me.		
I believe that I am the original inventor or an original joint inventor of a claimed invention in the application.				
I hereby acknowledge that any willful false statement made in this declaration is punishable under18 U.S.C. 1001 by fine or imprisonment of not more than five (5) years, or both.				
In consideration of the payment by	UNITED MICROELECTROI CORP.	NICS having a postal add	ress of	
No.3, Li-Hsin Road 2, Science	-Based Industrial Park, Hs	in-Chu City 300, Talwan	, R.O.C.	
(referred to as "ASSIGNEE"below) to I of the sum of One Dollar (\$ 1.00), the receipt of which is hereby acknowledged, andfor other good and valuable consideration.				
I hereby sell, assign and transfer to ASSIGNEE and the successors and assignees of the ASSIGNEE the entire right, title and interest in and to any and all improvements which are disclosed in the invention as above-identified application and, in and to, all Letters Patent to be obtained for said invention by the above application or any continuations, continuation-in-part, divisions, renewals, substitutes, or extensions thereof, and as to Letters Patent any reissue or re-examination thereof.				
I hereby covenant that no assignment, sale, agreement or encumbrance has been or will be made or entered into which would conflict with this assignment;				
I further covenant that ASSIGNEE will, upon its request, be provided promptly with all pertinent facts and documents relating to said invention and said Letters Patent and legal equivalents as may be known and accessible to I and will testify as to the same in any interference, litigation proceeding related thereto and will promptly execute and deliver to ASSIGNEE or its legal				
representatives any and all papers, in maintain, issue and enforce said app equivalents thereof which may be ne IN WINTNESS WHEREOF, I have he	olication, said invention and said I ecessary or desirable to carry out	Letters Patent and said the proposes thereof.	f signing)	
Note: An application data sheet (PTC inventive entity, must accompany this				

Page 1 of 6

NPO#NAU-P2405-USA:0 CUST#UMCD-2014-0646 F#NPO-P0002E-US1201 DSC0-103U011217

#### Docket No NAUP2405USA

Inventor: Shao-Wei Wang Date: JAN 2 7 2015

Signature: Shav-Wei Wang

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# COMBINE DECLARATION (37 CFR 1.63) FOR UTILITY OR DESIGN APPLICATION USING AN APPLICATION DATA SHEET (37 CFR 1.76) AND ASSIGNMENT

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☑ The attached application, or				
☐ United States application number		filed o	filed on	
☐ PCT international application	number	file	d on	
The above-identified application was	made or authorized to be ma	ide by me.		
I believe that I am the original invente application.	or or an original joint inventor	of a claime	d invention in	the
I hereby acknowledge that any willfu- under18 U.S.C. 1001 by fine or impri	I false statement made in this isonment of not more than five	declaration e (5) years,	is punishable or both.	
In consideration of the payment by	UNITED MICROELECTR CORP.	RONICS	having a pos	tal address of
No.3, Li-Hsin Road 2, Science	-Based Industrial Park, I	Hsin-Chu	City 300, Ta	aiwan, R.O.C
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good an		1. <b>00)</b> , the r	eceipt of whic	h is hereby
I hereby sell, assign and transfer to ASSIGNEE and the successors and assignees of the ASSIGNEE the entire right, title and interest in and to any and all improvements which are disclosed in the invention as above-identified application and, in and to, all Letters Patent to be obtained for said invention by the above application or any continuations, continuation-in-part, divisions, renewals, substitutes, or extensions thereof, and as to Letters Patent any reissue or re-examination thereof.				
I hereby covenant that no assignmer entered into which would conflict with	nt, sale, agreement or encumb n this assignment;	orance has I	peen or will be	made or
I further covenant that ASSIGNEE wi and documents relating to said inven known and accessible to I and will te related thereto and will promptly exec	ition and said Letters Patent a stify as to the same in any inte	nd legal eq erference, li	uivalents as m tigation proce	nay be
representatives any and all papers, in maintain, issue and enforce said app equivalents thereof which may be ne IN WINTNESS WHEREOF, I have he	lication, said invention and sa cessary or desirable to carry o	id Letters Pout the prop	atent and said oses thereof.	d (Date of signing)
Note: An application data sheet (PTC inventive entity, must accompany this				

Page 3 of 6

NPO#NAU-P2405-USA:0 CUST#UMCD-2014-0646 F#NPO-P0002E-US1201 DSC0-103U011217

### Docket No NAUP2405USA

Inventor: Shu-Ming Yeh

Signature: Shu-Ming Yeh

Date: JAN 2 7 2015

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# COMBINE DECLARATION (37 CFR 1.63) FOR UTILITY OR DESIGN APPLICATION USING AN APPLICATION DATA SHEET (37 CFR 1.76) AND ASSIGNMENT

#### Title of Invention:

# SEMICONDUCTOR STRUCTURE WITH A MULTILAYER GATE OXIDE AND METHOD OF FABRICATING THE SAME

As the below named inventor, I herel This declaration is directed to:	by declare that:		
☑ The attached application, or			
☐ United States application number		_filed on	, or
☐ PCT international application	number	filed on	
The above-identified application was	made or authorized to be made	by me.	
I believe that I am the original invento application.	or or an original joint inventor of a	a claimed invention in	ı the
I hereby acknowledge that any willful under18 U.S.C. 1001 by fine or impri	false statement made in this dessenment of not more than five (5	claration is punishabl ) years, or both.	e
	UNITED MICROELECTROI	NICS having a po	estal address of
No.3, Li-Hsin Road 2, Science	-Based Industrial Park, Hs	in-Chu City 300,	Гаiwan, R.O.C.
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good and		00), the receipt of whi	ich is hereby
I hereby sell, assign and transfer to A the entire right, title and interest in an invention as above-identified applicat invention by the above application or substitutes, or extensions thereof, an	d to any and all improvements with and, in and to, all Letters Patany continuations, continuation-	hich are disclosed in tent to be obtained fo in-part, divisions, ren	the r said ewals.
l hereby covenant that no assignmen entered into which would conflict with	t, sale, agreement or encumbrar this assignment;	nce has been or will b	e made or
I further covenant that ASSIGNEE wi and documents relating to said invent known and accessible to I and will tes related thereto and will promptly exec	tion and said Letters Patent and stify as to the same in any interfe	legal equivalents as rence, litigation proc	mav be
representatives any and all papers, ir maintain, issue and enforce said appl equivalents thereof which may be ned IN WINTNESS WHEREOF, I have he	lication, said invention and said L cessary or desirable to carry out	etters Patent and sa	id f. (Date of signing)
Note: An application data sheet (PTO inventive entity, must accompany this	n/SB/14 or equivalent), including s form. Use this form for <u>each ad</u>	naming the entire ditional inventor.	

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F#NPO-P0002E-US1201 DSC0-103U011217

#### Docket No NAUP2405USA

LEGAL NAME OF INVENTOR(ASSIGNOR)				
Inventor:	Yu-Tung Hsiao	Date:	JAN 2 7 2015	
Signature:	Yn-Tung Hsiao			

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F#NPO-P0002E-US1201 DSC0-103U011217

RECORDED: 01/30/2015

NPO#NAU-P2405-USA:0

CUST#UMCD-2014-0646